AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of claims:

1. (previously presented) A III-V compound semiconductor having a first layer that comprises a first III-V compound semiconductor expressed by the general formula $In_uGa_vAL_wN$ where $0 \le u \le 1$, $0 \le v \le 1$, $0 \le w \le 1$, and $u+v+w=1$, a pattern on said first layer from a material different not only from said first III-V compound semiconductor but also from a second III-V compound semiconductor hereinafter described, and a layer on said first III-V compound semiconductor and said pattern from said second III-V compound semiconductor expressed by the general formula $In_xGa_yAl_zN$ where $0 \le x \le 1$, $0 \le y \le 1$, $0 \le z \le 1$, and $x+y+z=1$, wherein the full width at half maximum of the (0004) reflection X-ray rocking curve of said second III-V compound semiconductor is 700 seconds or less regardless of the direction of X-ray incidence, and the compound semiconductor is formed by a vapor phase epitaxy method.

2. (currently amended) A III-V compound semiconductor having a first layer that comprises a first III-V compound semiconductor expressed by the general formula $In_uGa_vAL_wN$ where $0 \le u \le 1$, $0 \le v \le 1$, $0 \le w \le 1$, and $u+v+w=1$, a pattern on said first layer from a material different not only from said first III-V compound semiconductor but

also from a second III-V compound semiconductor hereinafter described, and a layer on said first III-V compound semiconductor and said pattern from said second III-V compound semiconductor expressed by the general formula $In_xGa_yAl_zN$ where $0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq z \leq 1$, and $x + y + z = 1$, wherein an upper surface of said pattern is not in contact with said second III-V compound semiconductor, and the compound semiconductor is formed by a vapor phase epitaxy method, wherein said pattern is formed from W (tungsten), Re (rhenium), Mo (molybdenum), Cr (chromium), Co (cobalt), Si (silicon), gold, Zr (zirconium), Ta (tantalum), Ti (titanium), Nb (niobium), nickel, platinum, V (vanadium), Hf (hafnium), and pd (palladium), BN (boron nitride), SiN_x (silicon nitride) or tungsten nitride.

3. (previously presented) A III-V compound semiconductor as set forth in claim 1 or 2, wherein said pattern is formed from W or tungsten nitride.

4. (previously presented) A III-V compound semiconductor as set forth in claim 1 or 2, wherein the first III-V compound semiconductor is expressed by the general formula $In_uGa_vAL_wN$ where $0 \leq u < 1$, $0 \leq v < 1$, $0.01 \leq w \leq 1$, and $u + v + w = 1$.

5. (previously presented) A III-V compound semiconductor as set forth in claim 1 or 2, wherein said pattern is a lamination comprising at least two layers which are contacting each other and made of different materials.

6. (previously presented) A III-V compound semiconductor as set forth in claim 1 or 2, wherein said pattern is a lamination comprising at least a layer made of W and a layer made of a material other than W.

7. (previously presented) A III-V compound semiconductor as set forth in claim 5, wherein said pattern is a lamination comprising at least a layer made of W and a layer made of SiO_2.

8. (previously presented) An electronic device comprising the III-V compound semiconductor as set forth in claim 1 or 2.

9. (previously presented) A light emitting device comprising the III-V compound semiconductor as set forth in claim 1 or 2.

10. (withdrawn) A method of making a III-V compound semiconductor comprising:

forming a layer from a first III-V compound semiconductor expressed by the general formula $In_uGa_vAL_wN$ where $0 \leq u \leq 1$, $0 \leq v \leq 1$, $0 \leq w \leq 1$, and $u+v+w=1$,

forming a pattern on said layer from a material different not only from said first III-V compound semiconductor but also from a second III-V compound semiconductor,

forming a layer on said first III-V compound semiconductor wherein said pattern from said second III-V compound semiconductor satisfies the general formula $In_xGa_yAl_zN$ where $0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq z \leq 1$, and $x+y+z=1$, wherein the full width at half maximum of the (0004) reflection X-ray rocking curve of said second III-V compound semiconductor is 700 seconds or less regardless of the direction of X-ray incidence,

wherein the III-V compound semiconductor is formed by a vapor phase epitaxy method.